

IN THE SPECIFICATION:

The specification as amended below with replacement paragraphs shows added text with underlining and deleted text with ~~striketrough~~.

Please AMEND paragraph [0027] as follows:

[0027] As illustrated in FIG. 2A, a buffer layer 21 is formed on the top surface of the first protective layer 12. As shown in FIG. 2B, a P or N type semiconductor layer 22 having a predetermined pattern and a gate insulation layer 23 covering the semiconductor layer 22 are formed on a top surface of the buffer layer 21. A gate electrode layer 24 corresponding to the semiconductor layer 22 and a first insulation layer 25 covering the gate electrode layer 24 are formed on a top surface of the gate insulation layer 23. Next, a TFT layer including a drain electrode 26 and a source electrode 27 is formed on the first insulation layer 25. The drain electrode 26 and the source electrode 27 penetrate the first insulation layer 25 and the gate insulation layer 23 and are electrically connected to opposite sides, respectively, of the semiconductor layer 22. Meanwhile, a first auxiliary electrode ~~28b~~28a is formed on a top surface of the first insulation layer 25 to face a second auxiliary electrode ~~28a~~28b, which is formed on a top surface of the gate insulation layer 23 during the formation of the gate electrode 24, thereby forming a capacitor 28. The ~~second~~first auxiliary electrode 28a is connected to the source electrode 27. Next, as illustrated in FIG. 2C, a second insulation layer 25a is formed on the top surface of the first insulation layer 25. A first electrode layer 29 is formed on a surface of the second insulation layer 25 to be electrically connected to the drain electrode 26. A third insulation layer 30 is formed on the top surface of the second insulation layer 25a such that the first electrode layer 29 is exposed. An organic layer 31 is formed on a top surface of the first electrode layer 29 using evaporation or printing. A second electrode layer 32, i.e., a cathode, is formed on a top surface of the organic layer 31 and the third insulation layer 30.

Please AMEND paragraph [0029] as follows:

[0029] After the organic electroluminescent unit 20 is completed on the top surface of the first protective layer ~~11~~12, as illustrated in FIG. 3, a second protective layer 13, i.e., a passivation layer, having heat resistance, chemistry resistance, and moisture resistance is formed on a top surface of the organic electroluminescent unit 20. The second protective layer 13 planarizes the top surface of the organic electroluminescent unit 20. After completing the second protective layer 13, as shown in FIG. 4, a flexible main substrate 15 is bonded onto a top surface of the

second protective layer 13 using an adhesive 14. The flexible main substrate 15 may be made of a synthetic resin or a thin glass. In addition, the flexible main substrate 15 may be made of a composite layer including multiple thin films in order to prevent permeation of oxygen or moisture. In this case, preferably, the main substrate 15 has a thickness of 20-500 μm .